

Optoelektronische Koppler

Opto-electronic couplers

Typ	Grenzdaten max. ratings			Empfänger receiver	Koppelement coupling element					$t_r; t_f$ (μs)
	U_R (V)	I_F (mA)	P_{tot} (mW)		U_{CE} (V)	U_R (V)	U_{IO} (kV)	Übertra- gungsfaktor	transmission factor	
MB 101	2	50	50	Fototransistor	15		5	4 %		5,0
MB 104 A	6	40	200	Fototransistor	70		4,3	40 %		2,0
MB 104 B	6	40	200	Fototransistor	70		4,3	100 %		2,0
MB 104 C	6	40	200	Fototransistor	70		4,3	160 %		2,0
MB 104 D	6	40	200	Fototransistor	70		4,3	240 %		2,0
MB 110	3	100	50	Fotodiode		50	2	0,2 %		0,05
MB 111	3	30	100	Fotodiode			2,8			0,1
MB 123	2	50	100	Fototransistor	15			4 %		5,0

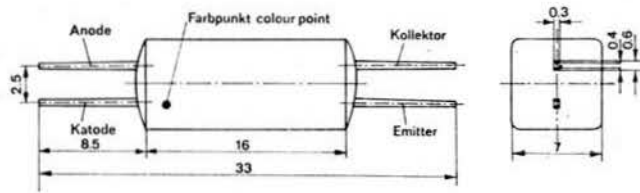
) typ. Wert

typ. value

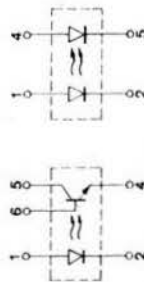
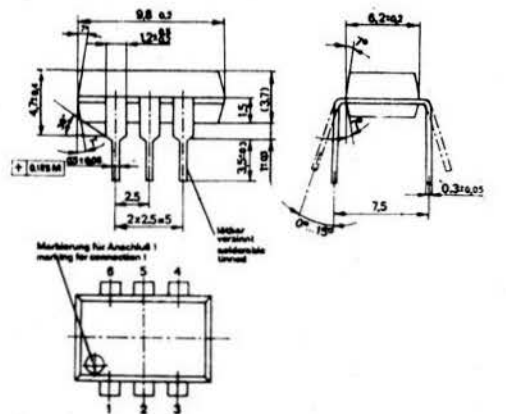
Infrarot-Emitterdioden

Infrared-emitting diodes

Typ	Grenzdaten bei max. ratings at $\vartheta_a = 25^{\circ}\text{C}$				Informationsdaten electrical characteristics bei $\vartheta_a = 25^{\circ}\text{C}$								
	P_{tot}	U_R	I_F	I_{FRM}	U_F	bei at I_F	λ_P	$\Delta\lambda$	I_s	bei at I_F	t_r	t_f	bei at I_{FRM}
	mW	V	mA	mA	V	mA	nm	nm	$\mu\text{W/sr}$	mA	ns	ns	mA
VQ 110	75	2	50	100	< 1,5	50	940	75	> 200	50	< 1000	< 1000	100
VQ 110 B									> 800	50			
VQ 110 C									> 1800	50			
									P_e				
									μW				
VQ 120 A	150	2	100	200	< 1,5	50	940	60	> 400	50	< 2000	< 2000	100
VQ 120 B									> 700	50			
VQ 120 C									> 1000	50			



MB 1C1

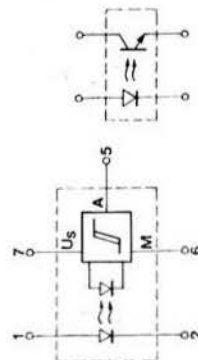
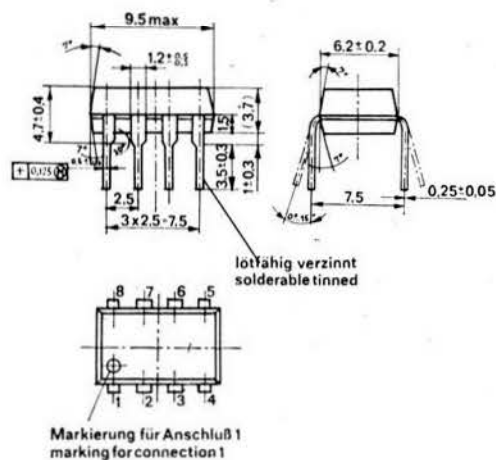


MB 104

MB 110

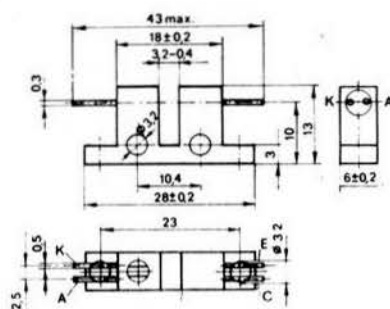
- | | | |
|---|------------------------|--------------------|
| 1 | IREDAnode | |
| 2 | IREDKatode | |
| 3 | nicht belegt | |
| 4 | Fototrans. (Emitter) | Fotodiode (Anode) |
| 5 | Fototrans. (Kollektor) | Fotodiode (Katode) |
| 6 | Fototrans. (Basis) | nicht belegt |

MB 104, MB 110

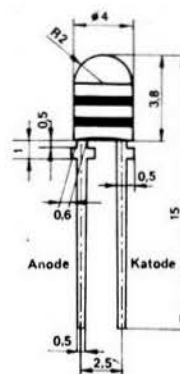


- 1 IRED-Anode
- 2 IRED-Katode
- 3 nicht belegt
- 4 nicht belegt
- 5 IS – Ausgang Y
- 6 IS – Masse
- 7 IS – Betriebsspannung
- 8 IS – Innere Verbindung

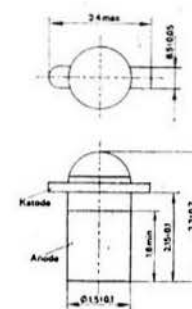
MB 111



MB 123



VQ 110



VQ 120